# MSKSEMI 美森科







TVC



TO



MOV



GDT



PIFD

# ESD9N5V-2-MS

**Product specification** 





#### **Feature**

- 100W peak pulse power per line (tP =8/20µs)
- DFN1006-2L package
- Replacement for MLV(0402)
- Unidirectional configurations
- Response time is typically < 1 ns</li>
- Protect one I/O or power line
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to
- IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact);
   IEC 61000-4-4 (EFT) 40A (5/50ns)

## **Applications**

- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, andservers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

### **Mechanical Characteristics**

- Mounting position: Any
- Qualified max reflow temperature:260 ℃
- Device meets MSL 1 requirements
- DFN1006-2L without plating

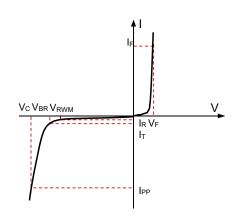
## **Reference News**

| PACKAGE OUTLINE | Circuit Diagram | Marking |
|-----------------|-----------------|---------|
|                 | Pin 1 Pin 2     | PU      |
| DFN1006-2L      |                 |         |



## **Electronics Parameter**

| Symbol          | Parameter                          |  |
|-----------------|------------------------------------|--|
| VRWM            | Peak Reverse Working Voltage       |  |
| <b>I</b> R      | Reverse Leakage Current @ VRWM     |  |
| V <sub>BR</sub> | Breakdown Voltage @ I⊤             |  |
| lτ              | Test Current                       |  |
| <b>I</b> PP     | Maximum Reverse Peak Pulse Current |  |
| Vc              | Clamping Voltage @ IPP             |  |
| P <sub>PP</sub> | Peak Pulse Power                   |  |
| CJ              | Junction Capacitance               |  |
| F               | Forward Current                    |  |
| VF              | Forward Voltage @ IF               |  |



# Electrical characteristics per line@25℃( unless otherwise specified)

| Parameter               | Symbol     | Conditions                    | Min. | Тур. | Max. | Units |
|-------------------------|------------|-------------------------------|------|------|------|-------|
| Working Voltage         | VRWM       |                               |      |      | 5    | V     |
| Breakdown Voltage       | VBR        | l <sub>t</sub> = 1mA          | 6    | 6.8  | 7.2  | V     |
| Reverse Leakage Current | <b>I</b> R | V <sub>RWM</sub> =5V          |      |      | 1    | μA    |
| Forward Voltage         | VF         | I⊧ = 10mA                     |      | 0.8  |      | V     |
| Clamping Voltage        | Vc         | IPP=1A tP = 8/20μs            |      |      | 9.0  | V     |
| Clamping Voltage        | Vc         | IPP=5A tP = 8/20µs            |      |      | 11.0 | V     |
| Junction Capacitance    | Cj         | V <sub>R</sub> =0V f = 1MHz   |      | 30   | 40   | pF    |
| Junction Capacitance    | Cj         | V <sub>R</sub> =2.5V f = 1MHz |      | 22   | 30   | pF    |

# Absolute maximum rating@25℃

| Rating                           | Symbol | Value        | Units |
|----------------------------------|--------|--------------|-------|
| Peak Pulse Power ( t₂ = 8/20μS ) | Ppp    | 100          | W     |
| Lead Soldering Temperature       | TL     | 260 (10 sec) | °C    |
| Operating Temperature            | TJ     | -55 to 125   | °C    |
| Storage Temperature              | Тѕтс   | -55 to 150   | °C    |



# **Typical Characteristics**

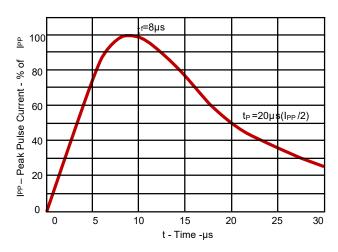


Fig 1.Pulse Waveform

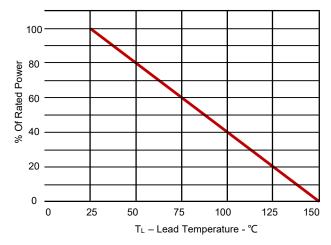


Fig 2.Power Derating Curve

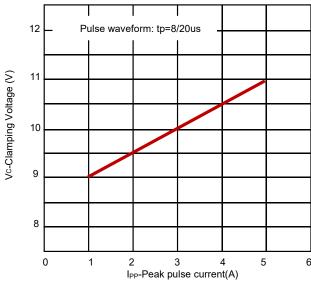


Fig 3. Clamping voltage vs. Peak pulse current

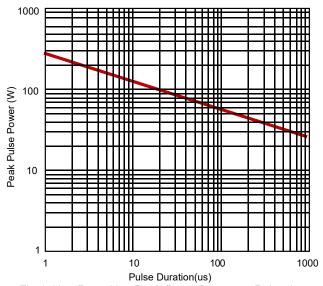
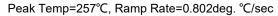
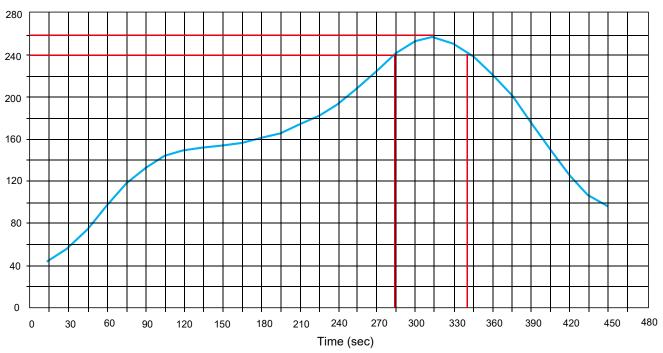


Fig 4. Non Repetitive Peak Pulse Power vs. Pulse time



#### **Solder Reflow Recommendation**





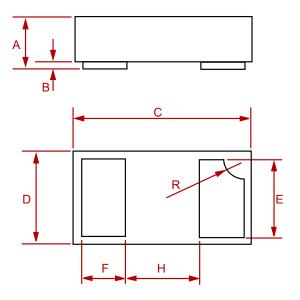
#### **PCB Design**

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

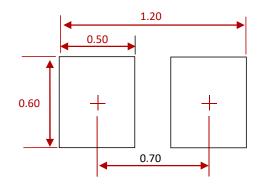


### **PACKAGE MECHANICAL DATA**



| Dim | Inches    |       | Millimeters |       |  |
|-----|-----------|-------|-------------|-------|--|
| Dim | MIN       | MAX   | MIN         | MAX   |  |
| Α   | 0.0125    | 0.02  | 0.32        | 0.52  |  |
| В   | 0.000     | 0.002 | 0.00        | 0.05  |  |
| С   | 0.037     | 0.043 | 0.95        | 1.080 |  |
| D   | 0.022     | 0.027 | 0.55        | 0.680 |  |
| E   | 0.016     | 0.024 | 0.40        | 0.60  |  |
| F   | 0.008     | 0.012 | 0.20        | 0.30  |  |
| Н   | 0.015Typ. |       | 0.40        | Тур.  |  |
| R   | 0.001     | 0.005 | 0.05        | 0.15  |  |

## **Suggested Pad Layout**



#### NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

## **REEL SPECIFICATION**

| P/N          | PKG        | QTY   |
|--------------|------------|-------|
| ESD9N5V-2-MS | DFN1006-2L | 10000 |



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